

# DFM Challenges and Practical Solutions in 65nm and 45nm

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## INTRODUCTION

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## Agenda

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- 0930-1000 Introduction (Kahng)
- 1000-1100 Test Structures, Test Chips, Design Style for 65nm, 45nm (Smayling)
- 1100-1130 Break
- 1130-1300 Interconnect Process Variations and RC Extraction (Nagaraj)
- 1300-1430 Lunch
- 1430-1600 Challenges and Opportunities for Design in Nano-CMOS Technologies (Wong)
- 1600-1630 Break
- 1630-1745 Manufacturing-Aware, Model-Driven Design Optimizations at 65nm and 45nm (Kahng)
- 1745-1800 Final Q&A

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Note: Updated slides at <http://vlsicad.ucsd.edu/>

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## What's New in EDA tools for DFM (Schoellkopf, STMicroelectronics, DAC-06)

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- **Big Foundry gives access to its “fab data” through encrypted standard format. Any CAD tool can now read those previously “secret” data to implement:**
  - Critical Area Analysis (and corrections)
  - Lithography Compliant Checks (and corrections)
  - CMP Checks (for parasitic extraction and dummy fill)
- **EDA and Foundries+IDMs collaborate for win-win situation: help the designer to get better chips (better yield, less power, more accurate timing) from manufacturing.**
- **More and more tools are DFM-aware:**
  - Litho-aware routers
  - Litho-aware and CMP-aware RC extractors
  - Variability handled by Statistical approach (Timing Analysis)

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## What's New in EDA tools for DFM (Schoellkopf, STMicroelectronics, DAC-06)

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- **Lithography Simulators, like DRC tools, are now ready for new computer architectures (multi-thread, multi-core, multi-processor)**
  - Can handle bigger designs in shorter times
  - Can do incremental modifications
  - Can do more verifications
- **At 90nm, Timing Closure was (is) the challenge**
- **At 65nm, DFM Closure is (already) the challenge**

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## DFM Activity In Academia

### ■ Moving from the mechanics of SSTA to the question of how to feed statistical design tools

- This is a very tough issue
- More work on test structure design, and how to extract useful variational or process models from measured data
- Some “open model” kinds of initiatives

### ■ Rediscovering the issue of “closing the loop” between lithography simulation and electrical performance

- Goal = “shape-to-electrical” transform that builds on existing LPC (litho process check), hotspot finding, etc. litho-sim capability
- Again, this is a very tough issue → **e.g., What happens to SPICE corners !?!**

### ■ “Grand unification” of DFM/DFY with test getting traction

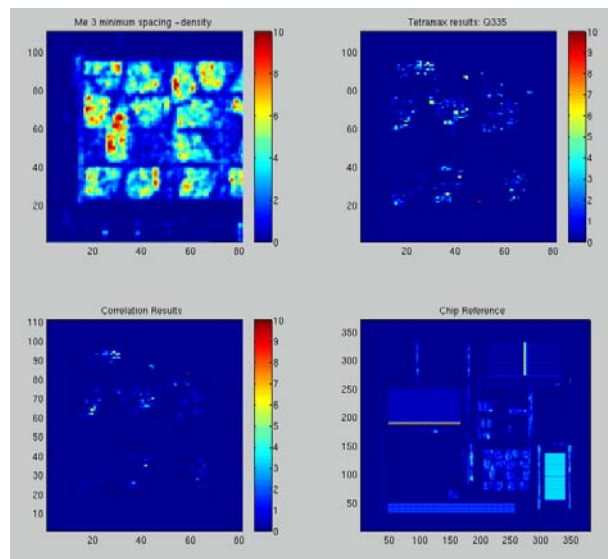
- Lots of data in the fab's YMS (yield management system) that remains unconnected to design issues such as constraints and signoff.
- Mismatches between silicon and models / signoff analyses are very costly
- **Eventually, need to be able to modulate the process to fit the design sweet spot (rather than only the other way around)**

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## Example: Hot Spots versus Volume Diagnosis



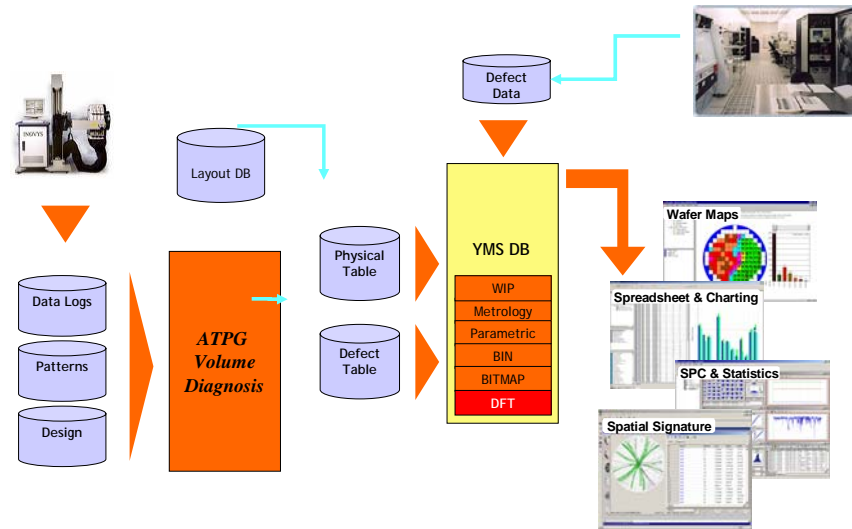
Courtesy of Davide Appello, ST (DFM&Y 2006)

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## Picture of Test-DFM Closure



Courtesy of Davide Appello, ST (DFM&Y 2006)

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## DFM Activity In Academia

### ■ Many new concerns and distractions

- **Reliability (TDDDB, NBTI, SEU, ...) = concern**
- **Stress = concern**
- **Beyond-CMOS = distraction**
  - CNTs
  - Bio-chips
  - QCAs
- **“More Than Moore” = critical, but not so much in scope of DFM**
  - Stacking/3D/SIP integration
  - Microarchitecture (multi-core, networks on chip)
  - Memory hierarchy
  - Design productivity (convergence, QOR, ...)

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## DFM Activity In Industry

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### ■ Foundries are thinking about opening up ... slightly

- TSMC DDK (DFM Design Kit), Open Model Initiative, ...
- Goal: allow fabless customers to access data in encrypted / arm's-length ways
- **Issue:** Metrics, competition/IP, business contract w/fabless
- **Issue:** SPICE model and RCX model guardbanding

### ■ First wave of DFM “golden validations” has arrived

- CMP simulation, litho simulation, critical area analysis, etc.
- In theory, lays groundwork for new optimizations that don't necessarily need expensive silicon experiments to be seen as having value.
- Integrated simulators (litho, CMP) will be provided/supported by foundries to enable accurate prediction of performance
  - “Process-Aware Timing” flows, etc. → **but these are currently broken !!!**
- **Issue:** what is the ROI from using such tools?
- **Issue:** SPICE, RCX guardband for signoff !!!
  - “Process-Aware Timing”: foundry must sign up to variant BC, WC corners!
  - With new “golden validations”: greater manufacturing-friendliness (RDR, CMP) gets rewarded by the fab? (tighter timing, power corners in signoff?)

## DFM Activity In Industry

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### ■ Some silicon successes for DFM

- Still mostly in IDMs
- Specialized products (high-volume custom): memory, FPGA, etc.

### ■ Understanding that analysis or simulation alone is not showing enough value

- → DFM companies moving towards optimization
- Electrical and performance issues at the forefront
- Highest value comes from combining electrical + optimization
- Leakage still a dominant concern

### ■ RDRs (radically restricted design rules) cause unnecessary discussion of value proposition of DFM

- With RDRs, will variation decrease so that DFM will not be needed?
- No solid method of measuring cost vs. benefit from RDRs
- Still see resistance to RDRs in 45nm consumer (LP) processes
  - Density and cost are still drivers
- 32nm almost certainly requires RDRs (even with many costly tricks)

## The Way Things Were

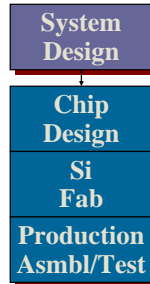
### ■ Trend for de-verticalization of the Industry

- Business Trade Offs : economy of scale vs. control
- Technical Trade Offs : core competence vs. integration

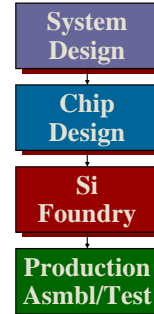
#### Vertical Entity



#### IDM



#### Fabless/Foundry



### ■ Foundry-Fabless Model Enabled by Commoditization

- e.g. General purpose process technology to service many product lines
- e.g. Standard (practical) handoffs between process and design

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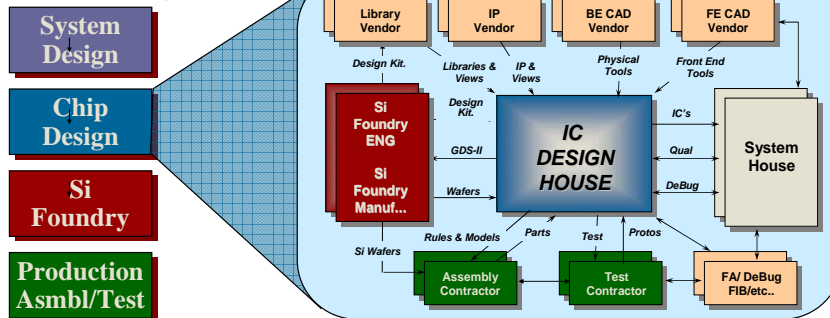
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## Fabless Model is a Bit More Complicated

### ■ Extensive Interface Management Challenges

- Managing a diversity of business models in a supply chain
- Managing a diversity of technical specialties

#### Fabless/Foundry



### ■ The Real Challenge is When Things do not Work

- Ultimately the Chip House "holds the bag"
- Not a show stopper in established technologies and design flows because things mostly work

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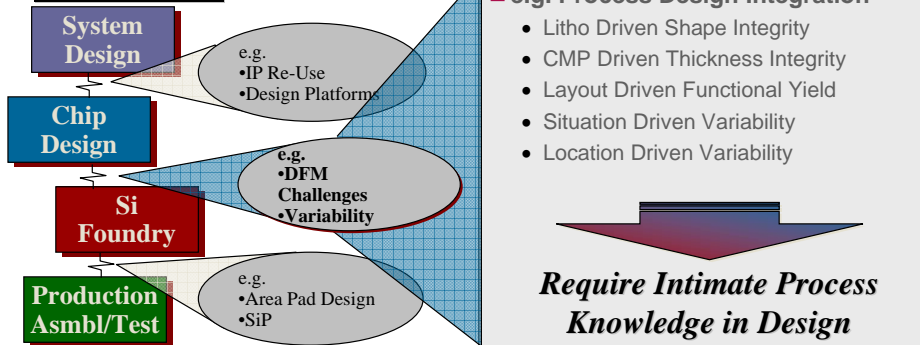
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## Challenges at the Leading Edge

### ■ Growing Integration Challenges with Traditional Fabless Model

- Technical Challenges : Process-Design Integration at ~65 and below
- Business Challenges : cost of design on (b)leading edge

#### Fabless/Foundry



### ■ e.g. Process Design Integration

- Litho Driven Shape Integrity
- CMP Driven Thickness Integrity
- Layout Driven Functional Yield
- Situation Driven Variability
- Location Driven Variability

**Require Intimate Process Knowledge in Design**

### ■ At Advanced Nodes it is Increasingly Hard to Make Things Work

- And the business pressures do not make trade offs any easier
- It would seem that IDM model has an intrinsic technical advantage

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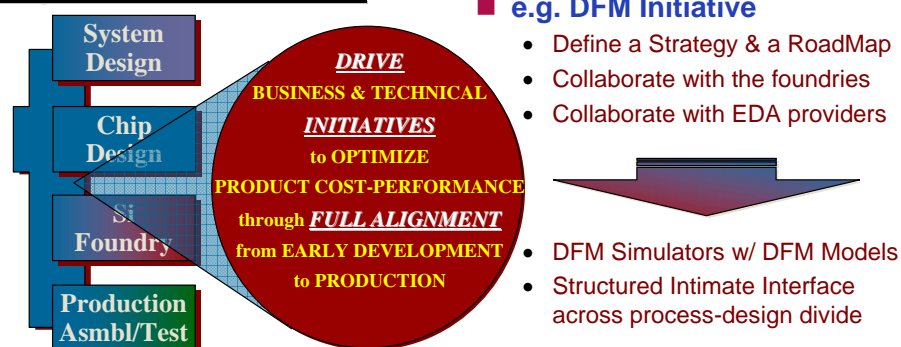
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## Integrated Fabless Manufacturer

### ■ Integrating and Aligning the Supply Chain

- Technical Challenges : coordinated development to optimize a product
- Business Challenges : supporting a collaborative effort

#### Integrated Fabless Manufacturer



### ■ e.g. DFM Initiative

- Define a Strategy & a RoadMap
- Collaborate with the foundries
- Collaborate with EDA providers
- DFM Simulators w/ DFM Models
- Structured Intimate Interface across process-design divide

### ■ Aligned Technology Chain : through collaboration NOT ownership

- Best of Both Worlds : Business advantages and flexibility of the fabless world with technical alignment and integration of the IDM world

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## The Way Things Are

### ■ Bifurcation of the Traditional Fabless Model : IFM

- Required for leadership on the leading edge
- Best of Both Worlds

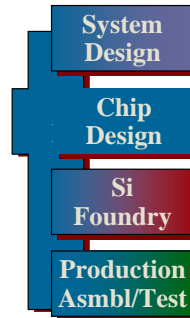
#### Vertical Entity



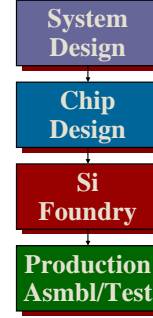
#### IDM



#### IFM



#### Fabless/Foundry



### ■ Integrated Fabless Manufacturer

- An approach for leadership in the fabless sector
- Good for Qualcomm, good for the industry

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## DFM Survival Principles

### ■ Don't assume what doesn't exist

- "detailed process information", "statistics" to feed statistical tools, ...

### ■ Manufacturing process is not stable

- Try to use trends rather than numbers

### ■ Preserve the flow!

- Design teams already spent \$MM to make production flows
- Generalization: Don't mess with anything that's golden

### ■ Don't make improvements that aren't significant enough to be measured

- Full silicon A-B experiment costs ~\$2M
- Simulation is never sufficient proof

### ■ Separation of concerns is a good thing

- Don't assume "new silicon IC designer" (= deep + broad)
- → Abstract interfaces (rather than "break down barriers")

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## DFM Reality Checks

- Communication of variation will be simpler and later than anticipated
- Designers and foundry also solve the problem!
  - Regular layout practices (e.g., on device layers)
  - Fab continuously reduces variation – ECMP, RDR, ...
- Size of opportunities is misunderstood
  - How much variation is systematic intra-/inter-die?
  - How different is the statistical optimization result from the deterministic optimization result?
- Difficult modeling / infrastructure challenges
  - E.g., correlation model that says 1 buffer = 2 inverters?
  - ‘Deconvolution’ problems (RCX/CMP, LPC/LPE, ...)

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## Key Issues to Track Going Into 45nm and Beyond

- **Business**
  - Value proposition / ROI for adoption of DFM by design teams
  - Consensus on models, DFM-score, etc. standards
  - Correctly working and usable flows (integrated platforms)
  - Migration path to those flows
- **Technology**
  - Parametric yield optimization becomes a reality
  - DFM/DFY connections to YMS, DFT (e.g., silicon-signoff correlation)
  - Stress modeling and exploitation
  - DFM for the interconnect stack (BEOL)
  - Much more DFM in floorplan, physical synthesis, P&R (+ analysis support)
  - Support for restricted layout
    - Guardband reduction
    - Improved routers
    - 32nm support: Layout decomposition or grating-based layout
  - Lots of “connecting the dots” (CMP, litho, CAA, device performance, device reliability, ...)

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## What Else?

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- What are the key trends and questions in YOUR view?
- Moving DFM up in the design chain – e.g., to functional level (before physical level)
- DFM at fault analysis stage – how to correct current design?

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